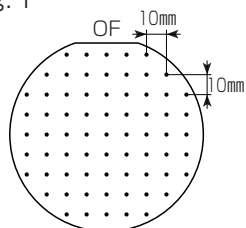


GaAs Single Crystal Wafers (Semi-Insulating Type)

Standard Specifications

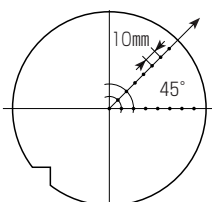
Conduction Type	Semi-Insulating			
Growth Method · Dopant	VB · C-Controlled			
Use	for Epi.		for Ion-Implantation	
Carbon Concentration (cm ⁻³)	Controlled (0.5~20×10 ¹⁵)		Controlled (0.5~3×10 ¹⁵)	
Carrier Concentration (cm ⁻³)	≤1×10 ⁸			
Resistivity (Ω · cm)	≥8×10 ⁷		1~4×10 ⁷	
Mobility (cm ² /V · sec)	≥3000		≥6000	
EPD Average (cm ²)	≤5000	≤10000	≤5000	≤10000
Measuring Points of EPD	Fig.1	Fig.2	Fig.1	Fig.2
Diameter (mm)	100.0±0.3	150.0±0.3	100.0±0.3	150.0±0.3
OF (mm) (Fig.3)	32.5±1.0	Notch (*3) (SEMI Standards)	32.5±1.0	Notch (*3) (SEMI Standards)
IF (mm) (Fig.3)	18.0±1.0		18.0±1.0	
Edge Rounding (mmR)	0.25 (Conform to SEMI Standards)			
Thickness (μm)	625±25	675±25	625±25	675±25
Orientation	(100) ±0.3°, (100) 2° off <110> ±0.3°			
Surface Finish	P/P			
Surface Clean	SC+ (Super Clean Plus)			
Flatness · LPD (*1)	Refer to Page 8			
Package (*2)	Cassette			

Fig. 1



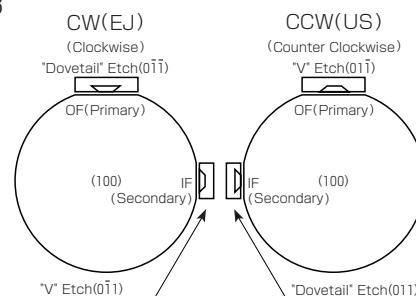
4" φ : 69 Points

Fig. 2



6" φ : 15 Points

Fig. 3



Notes

- (*1) LPD : Light Point Defects
- (*2) Individual Container is also available.
- (*3) Notch : Axis [010], Depth 1mm, Angle 90°

Attached Data

- Standard : Resistivity · Mobility · Diameter · OF · IF · Thickness · Flatness (min.~max.)
- Option : EPD Map · Accuracy of Orientation · Light Point Defects